

INFORMATION DISCLOSURE
CITATION

ATTY. DOCKET NO.

925-178

APPLICANT

NAKAMURA et al.

FILING DATE

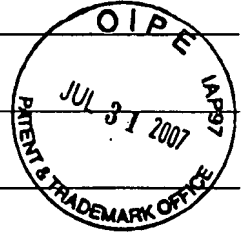
May 1, 2000

SERIAL NO.

09/463,643

GROUP

2815



(Use several sheets if necessary)

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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*Examiner

Date Considered

10/07

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Sheet 11 of 11

FORM PTO-1449
(Modified)

U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No.: NICHIA-00700 Serial No.: 09/463643

Applicant: Shuji Nakamura, *et al.*

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(37 CFR § 1.98(b))

NS	WO9857378A1	12/17/98	PCT	HOIL	29/73	
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